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# ABSTRACT OF THE DISCLOSURE

A plasma etching apparatus includes a worktable disposed in a hermetic process chamber. The worktable has a main surface for placing a wafer thereon, and a sub-surface for placing a focus ring thereon. A cooling mechanism for supplying cold to the main surface and sub-surface is disposed in the worktable. A heat transfer medium made of conductive silicone rubber is interposed between the sub-surface and focus ring. A press mechanism presses the focus ring toward the sub-surface. The heat transfer medium improves thermal conductivity between the sub-surface and focus ring to be higher than in a case with no thermal transfer medium.